

L Number	Hits	Search Text	DB	Time stamp
-	23385	transistor and ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) with gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:06
-	6093	(transistor and ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) with gate)) and (silicon with (wafer substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:11
-	5427	((transistor and ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) with gate)) and (silicon with (wafer substrate))) and (silicon adj nitride nitriding nitrogen nitrogen adj (atmosphere ambient) metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:35
-	3752	((transistor and ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) with gate)) and (silicon with (wafer substrate))) and (silicon adj nitride nitriding nitrogen nitrogen adj (atmosphere ambient) metal)) and (anneal\$3 heat\$3 thermal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:36
-	39618	(method process forming) with metal adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:05
-	2098	((method process forming) with metal adj oxide) and (nitride with (substrate wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:12
-	2121	((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:47
-	1055	((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:12
-	948	((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and (anneal\$3 heat\$3 thermal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:13
-	88	((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and ((anneal\$3 heat\$3 thermal) with laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:50
-	65	((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and ((anneal\$3 heat\$3 thermal) with laser)) and (silicon with (wafer substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:51
-	5	((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and ((anneal\$3 heat\$3 thermal) with laser)) and (silicon with (wafer substrate))) and (atmosphere ambient nitrogen hydrogen source drain s/d)) and (transistor and ((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) with gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 13:55

-	62	((((method process forming) with metal adj oxide) and ((nitride nitriding nitridation)with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and ((anneal\$3 heat\$3 thermal) with laser)) and (silicon with (wafer substrate))) and (atmosphere ambient nitrogen hydrogen source drain s/d)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 14:02
-	16285	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near5 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:08
-	13201	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near4 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:09
-	9688	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near3 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:09
-	5722	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near2 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:10
-	2376	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:11
-	761	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:12
-	199	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:12
-	92	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:13
-	92	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and (oxydation oxydiz\$3 oxygen 'O2')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:13
-	84	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and (oxydation oxydiz\$3 oxygen 'O2')) and (anneal\$3 heat\$3 thermal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:16
-	8	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and (oxydation oxydiz\$3 oxygen 'O2')) and (anneal\$3 heat\$3 thermal)) and metal adj oxide) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:17
-	58	((high adj k high adj3 dielectric high adj ("5304499").PN.) constant metal adj oxide) near gate)) and ((silicon 'SOI' with (wafer substrate))) and (nitride with (substrate wafer))) and (oxydation oxydiz\$3 oxygen 'O2')) and (oxydation oxydiz\$3 oxygen 'O2')) and (anneal\$3 heat\$3 thermal)) and metal adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/31 15:44

-	12	"6020024"	USPAT	2002/05/31 15:45
-	1	"6037235".PN.	USPAT	2002/05/31 16:07
-	1	"6037235".PN.	USPAT	2002/05/31 16:57
-	1	"5716875".PN.	USPAT	2002/05/31 16:57
-	1	"5629043".PN.	USPAT	2002/05/31 16:57
-	1	"6037235".PN.	USPAT	2002/05/31 16:57
-	1	"5716875".PN.	USPAT	2002/05/31 16:57
-	1	"5629043".PN.	USPAT	2002/05/31 16:57
-	1	"5629043".PN.	USPAT	2002/05/31 16:57
-	1	"5591681".PN.	USPAT	2002/05/31 16:58
-	1	"5550091".PN.	USPAT	2002/05/31 16:58
-	1	"5405801".PN.	USPAT	2002/05/31 16:58
-	1	"5405801".PN.	USPAT	2002/05/31 16:58



Active

- ☞ L3: (191) ((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)
- ☞ L4: (2561) nitrogen with (sputtering 'RF' adj3 sputtering)
- ☞ L5: (16) 3 and 4
- ☞ L6: (16) (((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)) and (nit

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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6537428 B1	20030325	10	Stable high rate reactive sputtering	204/192.13	204/192.15;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6092669 A	20000725	12	Equipment for producing thin-film solar cell	204/298.13	204/192.16;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6048442 A	20000411	12	Method for producing thin-film solar cell and equipment for producing the	204/192.28	204/192.25
4	<input type="checkbox"/>	<input type="checkbox"/>	US 5891264 A	19990406	29	Solar cell and method for producing electrode for solar cell	136/261	204/192.26;
5	<input type="checkbox"/>	<input type="checkbox"/>	US 5798027 A	19980825	20	Process for depositing optical thin films on both planar and non-planar s	204/192.26	136/256;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 5711824 A	19980127	28	Solar cell	136/259	136/259
7	<input type="checkbox"/>	<input type="checkbox"/>	US 5578501 A	19961126	28	Method of manufacturing a solar cell by formation of a zinc oxide transpar	438/98	204/192.28;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5573884 A	19961112	18	Image-forming member for electrophotography	430/126	204/192.29;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 5420043 A	19950530	29	Method of manufacturing a solar cell	438/96	438/609;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 5401330 A	19950328	58	Photovoltaic element	136/259	430/95

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Active

L3: (191) ((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)

L4: (2561) nitrogen with (sputtering 'RF' adj3 sputtering)

L5: (16) 3 and 4

L6: (16) (((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)) and (nit

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(((solar photovoltaic) near3

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5573884 A	19961112	18	Image-forming member for electrophotography	430/126	430/95
9	<input type="checkbox"/>	<input type="checkbox"/>	US 5420043 A	19950530	29	Method of manufacturing a solar cell	438/96	204/192.29;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 5401330 A	19950328	58	Photovoltaic element	136/259	427/528;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 5324365 A	19940628	25	Solar cell	136/256	136/249;
12	<input type="checkbox"/>	<input type="checkbox"/>	US 5225057 A	19930706	21	Process for depositing optical films on both planar and non-planar substr	204/192.13	136/258;
13	<input type="checkbox"/>	<input type="checkbox"/>	US 4844719 A	19890704	22	Permeable polymer membrane for dessication of gas	95/52	136/258;
14	<input type="checkbox"/>	<input type="checkbox"/>	US 4673476 A	19870616	6	Antireflective film for photoelectric devices and manufacturing method th	204/192.28	136/259;
15	<input type="checkbox"/>	<input type="checkbox"/>	US 4511756 A	19850416	4	Amorphous silicon solar cells and a method of producing the same	136/258	204/192.12;
16	<input type="checkbox"/>	<input type="checkbox"/>	US 4471042 A	19840911	24	Image-forming member for electrophotography comprising hydro	430/64	204/192.15;
								136/256;
								204/192.25;
								136/258;
								252/501.1;

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Active

- ☞ L3: (191) ((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)
- ☞ L4: (2561) nitrogen with (sputtering 'RF' adj3 sputtering)
- ☞ L5: (16) 3 and 4
- ☞ L6: (16) (((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputtering)) and (nit

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3 and 4			

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6537428 B1	20030325	10	Stable high rate reactive sputtering	204/192.13	204/192.15;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6092669 A	20000725	12	Equipment for producing thin-film solar cell	204/298.13	204/192.16;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6048442 A	20000411	12	Method for producing thin-film solar cell and equipment for producing the	204/192.28	204/192.25
4	<input type="checkbox"/>	<input type="checkbox"/>	US 5891264 A	19990406	29	Solar cell and method for producing electrode for solar cell	136/261	204/192.26;
5	<input type="checkbox"/>	<input type="checkbox"/>	US 5798027 A	19980825	20	Process for depositing optical thin films on both planar and non-planar s	204/192.26	136/256;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 5711824 A	19980127	28	Solar cell	136/259	136/259
7	<input type="checkbox"/>	<input type="checkbox"/>	US 5578501 A	19961126	28	Method of manufacturing a solar cell by formation of a zinc oxide transpar	438/98	204/192.28;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5573884 A	19961112	18	Image-forming member for electrophotography	430/126	204/192.29;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 5420043 A	19950530	29	Method of manufacturing a solar cell	438/96	438/609;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 5401330 A	19950328	58	Photovoltaic element	136/259	430/95

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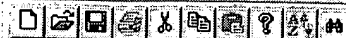
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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5573884 A	19961112	18	Image-forming member for electrophotography	430/126	430/95
9	<input type="checkbox"/>	<input type="checkbox"/>	US 5420043 A	19950530	29	Method of manufacturing a solar cell	438/96	204/192.29; 427/528;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 5401330 A	19950328	58	Photovoltaic element	136/259	136/249; 136/258;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 5324365 A	19940628	25	Solar cell	136/256	136/258; 136/259;
12	<input type="checkbox"/>	<input type="checkbox"/>	US 5225057 A	19930706	21	Process for depositing optical films on both planar and non-planar substr	204/192.13	204/192.12; 204/192.26
13	<input type="checkbox"/>	<input type="checkbox"/>	US 4844719 A	19890704	22	Permeable polymer membrane for dessication of gas	95/52	204/296; 521/27;
14	<input type="checkbox"/>	<input type="checkbox"/>	US 4673476 A	19870616	6	Antireflective film for photoelectric devices and manufacturing method th	204/192.28	204/192.12; 204/192.15;
15	<input type="checkbox"/>	<input type="checkbox"/>	US 4511756 A	19850416	4	Amorphous silicon solar cells and a method of producing the same	136/258	136/256; 204/192.25;
16	<input type="checkbox"/>	<input type="checkbox"/>	US 4471042 A	19840911	24	Image-forming member for electrophotography comprising hydro	430/64	136/258; 252/501.1;



- ☑ L4: (7) ((solar photovoltaic) near3 cell) with (('II-VI' 'CdTe' cadmium adj te
- ☑ L6: (183) ((solar photovoltaic) near3 cell) with (sputtering 'RF' adj3 sputteri
- ☑ L7: (15) 6 and (nitrogen with (sputtering 'RF' adj3 sputtering))
- ☑ L8: (68) ((solar photovoltaic) near3 cell) with ('II-VI')
- ☑ L9: (11917) ((solar photovoltaic) near3 cell)
- ☑ L10: (87) 9 and (nitrogen with (sputtering 'RF' adj3 sputtering))
- ☑ L11: (34) 10 and (nitrogen cadmium telluride sulfide selenide Zinc)
- ☑ L12: (0) (inert with sputtering) with (solar photovoltaic)
- ☑ L13: (1949) (inert with sputtering)
- ☑ L14: (0) (inert with sputtering) with Cadmium
- ☑ L15: (0) (inert with sputtering) same Cadmium
- ☑ L16: (0) (nitrogen with sputtering) same Cadmium
- ☑ L17: (31) (nitrogen with sputtering) same metallization

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(nitrogen with sputtering) same metallization

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6309967 B1	20011030	12	Method of forming a contact	438/658	438/656;
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6306762 B1	20011023	9	Semiconductor device having multi-layered metalization and method	438/648	438/661;
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6296747 B1	20011002	9	Baffled perforated shield in a plasma sputtering reactor	204/298.07	438/653;
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6255671 B1	20010703	10	Metal embedded passivation layer structure for microelectronic intercon	257/103	438/656
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6239029 B1	20010529	13	Sacrificial germanium layer for	438/688	204/298.11;
								204/298.14
								257/613;
								257/615;
								438/658;

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L1: (4) "5393675"

L2: (1) "5304499".PN.

L3: (1) "4650921".PN.

L5: (3) 4 and nitrogen

L4: (7) ((solar photovoltaic) near3 cell) with ((

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((solar photovoltaic) near3 cell) with ((('II-VI' 'CdTe' cadmium adj telluride) with (sputtering 'RF' adj3 sputtering))

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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6137048 A	20001024	14	Process for fabricating polycrystalline semiconductor thin-film solar cells, a	136/260	136/256; 136/265;	
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5714404 A	19980203		Fabrication of polycrystalline thin films by pulsed laser processing	438/94	438/487; 438/798;	
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5500056 A	19960319		Solar cell containing low melting point glass layer	136/259	136/256; 136/260;	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 5393675 A	19950228	8	Process for RF sputtering of cadmium telluride photovoltaic cell	438/95	136/260; 136/264;	
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4345107 A	19820817	13	Cadmium telluride photovoltaic cells	136/255	136/260; 136/264;	
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4261802 A	19810414	9	Method of making a photovoltaic cell	438/92	136/260; 205/170;	
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4260427 A	19810407	8	CdTe Schottky barrier photovoltaic cell	136/255	136/260; 257/449;	

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